

Silicon NPN Power Transistors

2N6493

DESCRIPTION

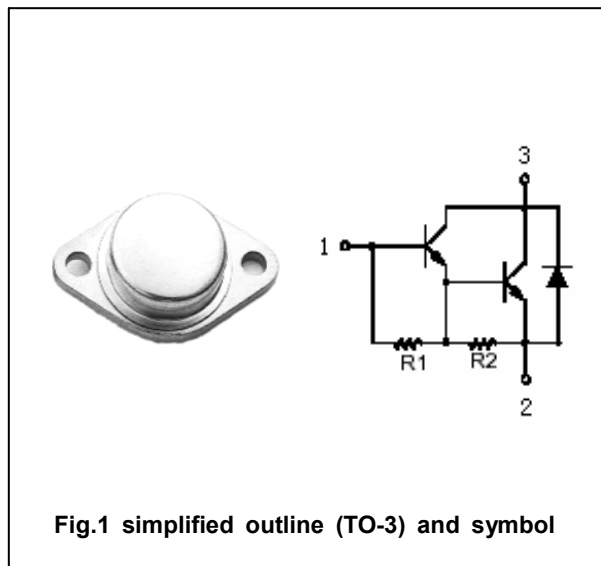
- With TO-3 package
- Low collector saturation voltage
- High DC current gain
- DARLINGTON

APPLICATIONS

- General-purpose power amplifier and low frequency swithing applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	70	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
P _D	Total Power Dissipation	T _C =25□	100	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.75	□/W

Silicon NPN Power Transistors

2N6493

CHARACTERISTICS

T_m=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0	70			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =100mA			3	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A ; I _B =100mA			4	V
V _{BE}	Base-emitter on voltage	I _C =4A ; V _{CE} =4V			2.8	V
I _{CEO}	Collector cut-off current	V _{CE} =50V; I _B =0			1.0	mA
I _{CEX}	Collector cut-off current	V _{CE} =100V; V _{BE(off)} =-1.5V			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3.0	mA
h _{FE-1}	DC current gain	I _C =4A ; V _{CE} =4V	500			
h _{FE-2}	DC current gain	I _C =15A ; V _{CE} =4V	100			

Silicon NPN Power Transistors

2N6493

PACKAGE OUTLINE

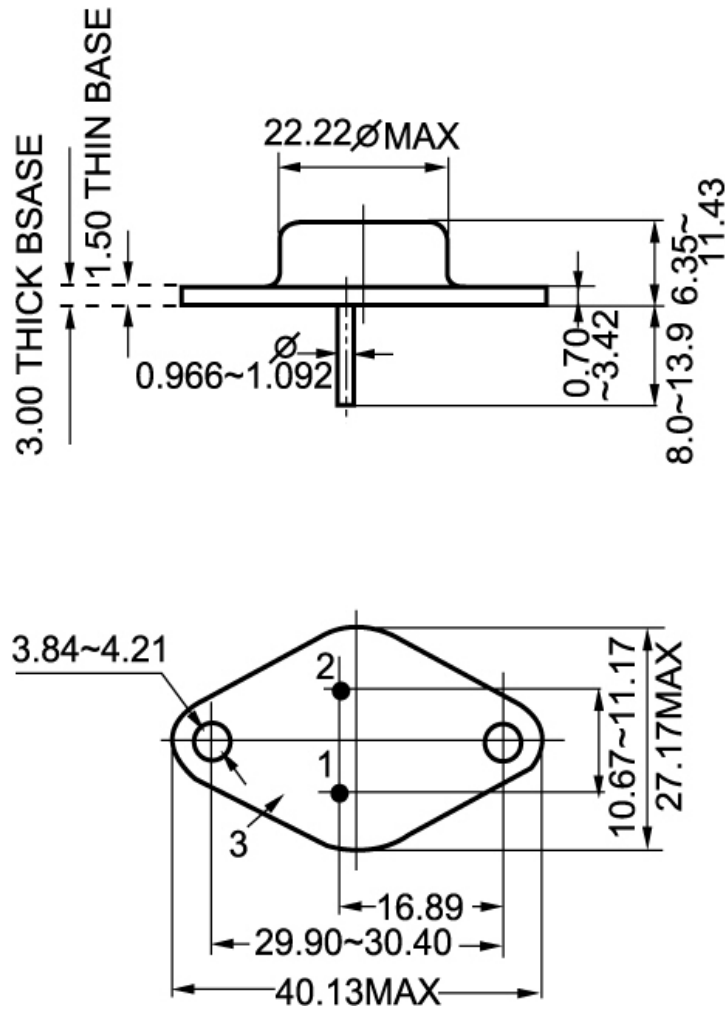


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)